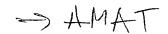


PATENT Atty. Dkt. AMAT/6392/DD/LOW K/JW Express Mail No. EV041915621US



ABSTRACT OF THE DISCLOSURE

A method is provided for processing a substrate including providing a processing gas comprising an organosilicon compound comprising a phenyl group to the processing chamber, and reacting the processing gas to deposit a low k silicon carbide barrier layer useful as a barrier layer in damascene or dual damascene applications with low k dielectric materials.